

	Type	Hits	Search Text	DBs
1	BRS	1473	((field with effect) or FET) and (metal with gate) and (conform\$5 with deposit\$3)	US-PGPUB; USPAT
2	BRS	1501	((field with effect) or FET) and (metal with gate) and (conform\$5 with deposit\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
3	BRS	0	S2 and (conductive with seed with layer) and (electroplat\$3 with gate with metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
4	BRS	0	S2 and (conductive with seed with layer) and (electroplat\$3 with gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
5	BRS	3	(conductive with seed with layer) and (electroplat\$3 with gate with metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
6	IS&R	1	("5912492").PN.	USPAT
7	BRS	1501	((field with effect) or FET) and (metal with gate) and (conform\$5 with deposit\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
8	BRS	3	(conductive with seed with layer) and (electroplat\$3 with gate with metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
9	BRS	0	S7 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
10	BRS	33	S7 and seed and electroplat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
11	BRS	2387	(MOSFET or FET) and (work with function) and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
12	BRS	1811	(MOSFET or FET) and (work adj function) and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
13	BRS	391	S12 and PMOS and NMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
14	BRS	9	S14 and (gate with electroplat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
15	BRS	302	S13 and (metal with gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
16	IS&R	1	("6015747").PN.	USPAT
17	BRS	69	metal with gate with electroplat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
18	BRS	2387	(MOSFET or FET) and (work with function) and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB

	Type	Hits	Search Text	DBs
19	BRS	58	S18 and Ru and Ta and alloy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
20	BRS	19	S18 and (Ru with Ta with alloy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
21	BRS	4	S18 and (Ru-Ta adj alloy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB
22	BRS	28	MOSFET with (gate adj size)	US-PGPUB; USPAT
23	BRS	449	(CMOS with gate with size)	US-PGPUB; USPAT
24	BRS	10258	gate with dimension	US-PGPUB; USPAT

	Type	Hits	Search Text	DBs
25	BRS	768	gate adj dimension	US-PGPUB; USPAT
26	BRS	30	MOSFET with gate adj dimension	US-PGPUB; USPAT
27	BRS	10	through-mask adj electroplating	US-PGPUB; USPAT
28	BRS	511	damascene with electroplating	US-PGPUB; USPAT
29	BRS	350	S28 and (seed adj layer)	US-PGPUB; USPAT
30	BRS	77	electroplating with Ru	US-PGPUB; USPAT
31	BRS	41	S30 and (seed adj layer)	US-PGPUB; USPAT
32	IS&R	1	("6204103").PN.	USPAT
33	BRS	171	MOSFET with (work adj function)	US-PGPUB; USPAT
34	BRS	6	S33 and Intel	US-PGPUB; USPAT
35	BRS	80	Lin.IN. and (work adj function)	US-PGPUB; USPAT

	Type	Hits	Search Text	DBs
36	BRS	0	S35 and Intel	US-PGPUB; USPAT
37	BRS	0	Linn.IN. and (work adj function)	US-PGPUB; USPAT
38	BRS	136	Intel and (work adj function)	US-PGPUB; USPAT
39	BRS	3118	257/204.ccls. or 438/197-199,217,218,587,642.ccls.	US-PGPUB; USPAT
40	BRS	237	S39 and (work with function)	US-PGPUB; USPAT
41	BRS	182	S40 and (gate with (metal or alloy))	US-PGPUB; USPAT